3DD10, 3DD11

NPN Silicon Low Frequency High Power Transistor

Features:

1. Using triple-diffusion process.Excellent capacity in anti-burnout.Excellent second breakdown capacity.
2. Good temperature stability.Excellent thermal fatigue capability.
2. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
3. Use for Low-speed switch,low frequency power amplify,power adjustment.
4. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA: **(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications								
			3DD10				3DD11				
			A	B	C	D	E	F	G	H	I
Collector-Emitter Voltage	V_{CEO}	V	50	100	150	200	250	300	400	500	600
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	50	100	150	200	250	300	400	500	600
			3DD10: I_C=5mA				3DD11: I_C=5mA				
Emitter-Base Voltage	V_{EBO}	V	5				5				
Max. Collector Current	I_{CM}	A	A~F≤20, G~I≤10				A~F≤30, G~I≤15				
Max. Collector Dissipation	P_{CM}	W	200 (T_C≤75°C)				300 (T_C≤75°C)				
Junction Temperature	T_{jm}	°C	175								
Storage Temperature	T_{stg}	°C	-55~+175								
Collector-Emitter Leakage Current	I_{CEO}	mA	5.0 (A:V_{CE}=30V;B:V_{CE}=50V; C~I:V_{CE}=100V)								
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	1.8(A~F: I_C=10A, I_B=1.0A) 2.0 (G~I: I_C=5.0A, I_B=1.0A)				2.0(A~F: I_C=15A, I_B=1.5A) 2.0 (G~I: I_C=7.5A, I_B=1.5A)				
DC Current Gain	h_{FE}		Max.:120 Min.:15(A~F: V_{CE}=5V, I_C=10A) Min.: 7 (G~I:V_{CE}=10V, I_C=5.0A)				Max.:120 Min.:15 (A~F: V_{CE}=5V, I_C=15A) Min.: 7 (G~I:V_{CE}=10V, I_C=7.5A)				
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	≥5 (I_E=15mA)				≥5 (I_E=15mA)				

h_{FE} Colored:

Color	Brown	Red	Orange	Yellow	Green	Blue
h_{FE}	7~15	15~25	25~40	40~55	55~80	80~120

Outline and Dimensions: